

## SK515B SCHOTTKY RECTIFIER

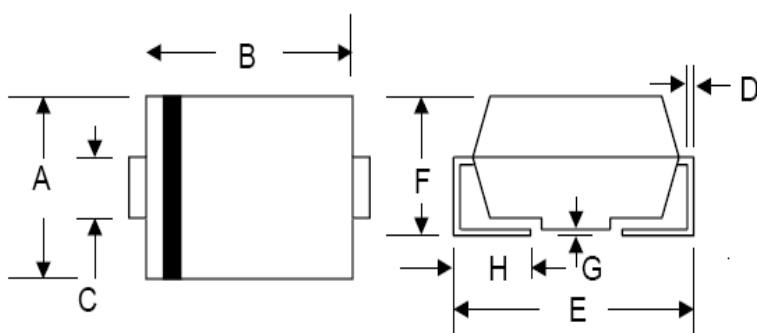
### Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

### Features:

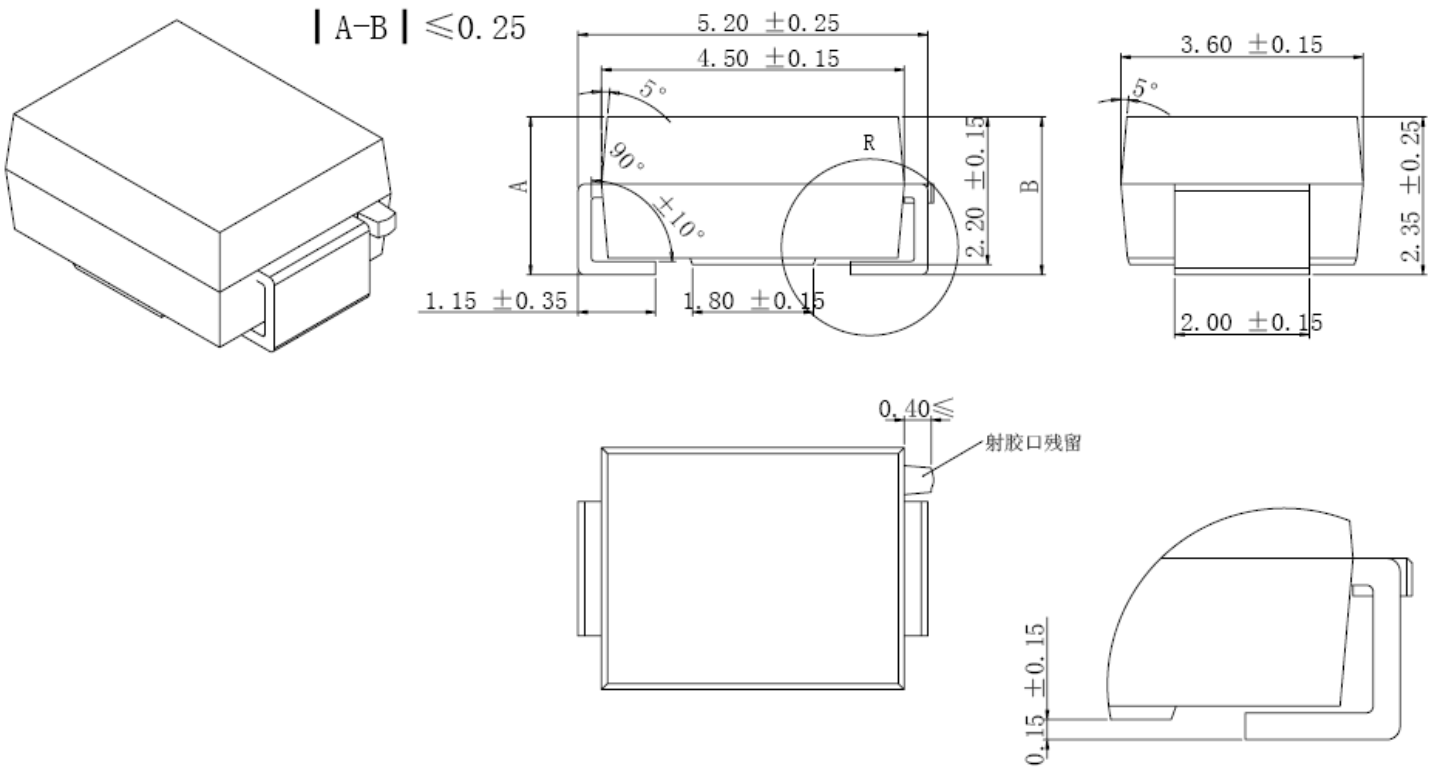
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Mechanical Dimensions: In mm



SMB/DO-214AA				
Dim	Min	Max	Min	Max
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.2	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
			in mm	In inch

### OPTION 1



**OPTION 2(JK)**

**SMB**



**Marking Diagram:**



Where XXXXX is YYWWL

- B = Package type
- 5 = Forward Current (5A)
- 15 = Reverse Voltage (150V)
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SK515B	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	150	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 145^\circ C$ , rectangular wave form	5	A
Max. peak one cycle Non-repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	120	A



**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	$V_{F1}$	@ 5A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.93	V
	$V_{F2}$	@ 5 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.80	V
Max. Reverse Current (per leg) *	$I_{R1}$	@ $V_R = \text{rated VR}$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated VR}$ $T_J = 125\text{ }^\circ\text{C}$	7.0	mA
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 4\text{V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	200	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/us

\* Pulse Width < 300 $\mu$ s, Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	-	4.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.68	g
Case Style	SMB			

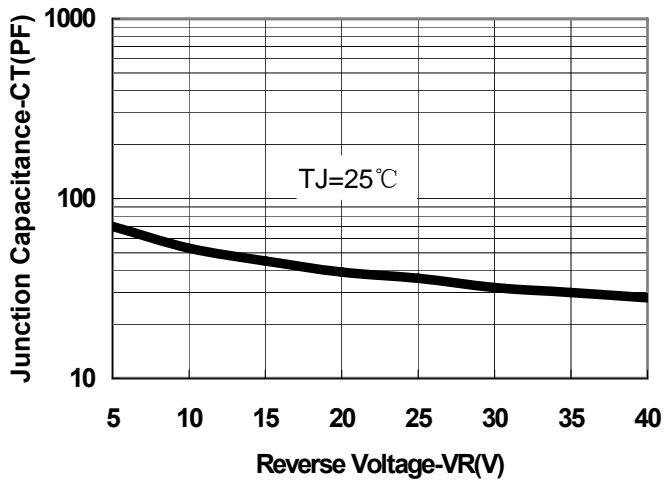


Fig.1-Typical Junction Capacitance Vs. Reverse Voltage

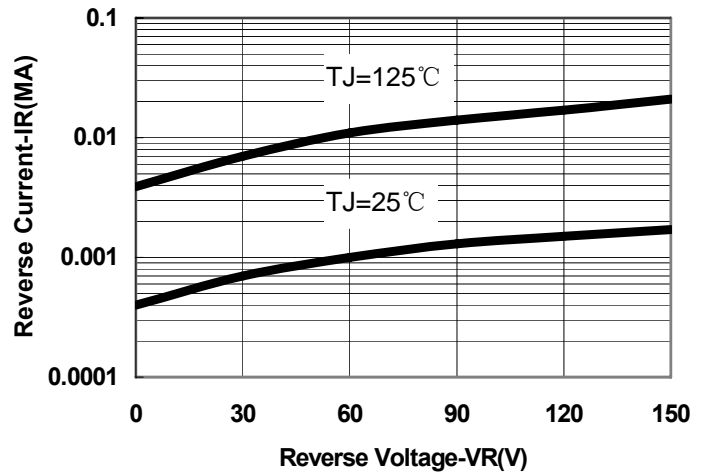


Fig.2-Typical Values Of Reverse Current Vs. Reverse Voltage

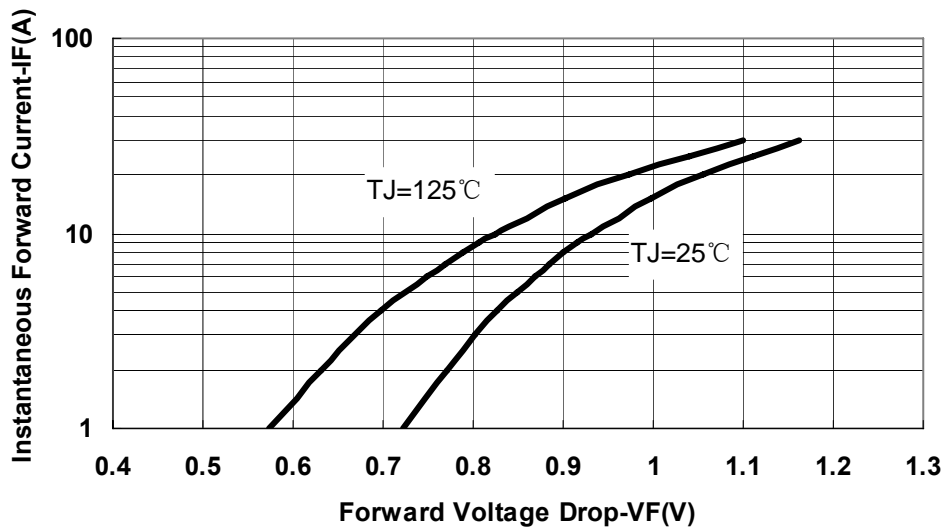


Fig.3-Typical Forward Voltage Drop Characteristics



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